WEST Search History

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DATE: Tuesday, February 14, 2006

Hide?	Set Name	Query	Hit Count
		DB=PGPB,USPT,USOC; PLUR=YES; OP=ADJ	
☐	L17	(tungsten silicide) with plasma with clean$3 with (hydrogen or 'H.sub.2')	2
☐	L16	L15 and ((chamber or apparatus or reactor) adj10 (clean$3 or etch$3 or remov$3) adj10 plasma)	60
☐	L15	(semiconductor or substrate or wafer or workpiece or device) same ((clean$3 or etch$3 or treat$3 or remov$3) adj10 (residue or $5resist or impurit$3 or polymer$3 or debris or 'SiO.sub.2')) same plasma same (hydrogen or 'H.sub.2') same (argon or Ar or He or helium or inert or Kr)	410
		DB=EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ	
☐	L14	L13 and ((chamber or apparatus or reactor) adj10 (clean$3 or etch$3 or remov$3) adj10 plasma)	2
☐	L13	(semiconductor or substrate or wafer or workpiece or device) same ((clean$3 or etch$3 or treat$3 or remov$3) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris or 'SiO.sub.2')) same plasma same (hydrogen or 'H.sub.2') same (argon or Ar or He or helium or inert or Kr)	29
☐	L12	(semiconductor or substrate or wafer or workpiece or device) with ((clean$3 or etch$3 or treat$3 or remov$3) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris or 'SiO.sub.2')) with plasma with (hydrogen or 'H.sub.2') with (argon or Ar or He or helium or inert or Kr)	9
		DB=PGPB,USPT,USOC; PLUR=YES; OP=ADJ	
☐	L11	L10 and ((chamber or apparatus or reactor) adj10 (clean$3 or etch$3 or remov$3) adj10 plasma)	21
☐	L10	(semiconductor or substrate or wafer or workpiece or device) with ((clean$3 or etch$3 or treat$3 or remov$3) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris or oxide or 'SiO.sub.2')) with plasma with (hydrogen or 'H.sub.2') with (argon or Ar or He or helium or inert)	79
☐	L9	l7 and ((chamber or apparatus or reactor) adj5 (clean$3 or etch$3) adj5 plasma)	8
☐	L8	L7 same ((silicon oxide) or (silicon dioxide) or 'SiO.sub.2')	13
☐	L7	(semiconductor or substrate or wafer or workpiece) same ((clean$3 or etch$3 or treat) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris)) same (plasma with (hydrogen or 'H.sub.2') with (argon or Ar or He or helium or inert))	107
☐	L6	L4 and l1	23
☐	L5	L4 and l4	7902
☐	L4	134/1,1.3,26,30;216/67,74;438/906.ccls.	7902
		DB=EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ	
☐	L3	L2 same ((chamber or apparatus) with (clean$3 or etch$3 or treat$3))	13

⌐ L2 (semiconductor or substrate or wafer or workpiece) with ((clean$3 or etch$3 or treat) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris)) with plasma with (hydrogen or 'H.sub.2') 37

DB=PGPB,USPT,USOC; PLUR=YES; OP=ADJ

⌐ L1 (semiconductor or substrate or wafer or workpiece) with ((clean$3 or etch$3 or treat) adj5 (residue or $5resist or impurit$3 or polymer$3 or debris)) with plasma with (hydrogen or 'H.sub.2') 96

END OF SEARCH HISTORY